

2SA634

Silicon PNP Transistors

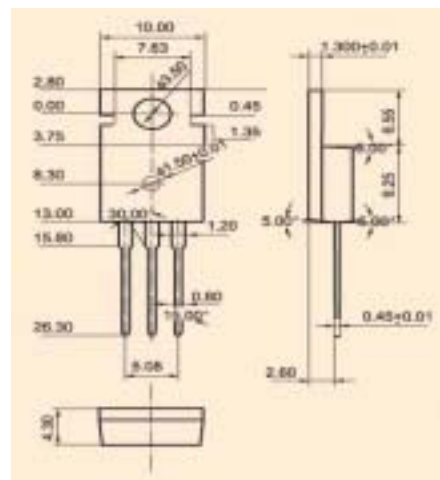


◆ Features

. With TO-220 package

◆ **Absolute Maximum Ratings Tc=25°C**

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	40	V
V_{CEO}	Collector to emitter voltage	40	V
V_{EBO}	Emitter to base voltage	5.0	V
I_B	Base collector current		A
I_C	Collector current	3.0	A
P_C	Collector power dissipation	10	W
T_j	Junction temperature	150	°C
T_{stg}	Storage temperature	-55~+150	°C



TO-220

◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
I _{CBO}	Collector-base cut-off current	V _{CB} =40V; I _E =0			200	uA
I _{EBO}	Emitter-base cut-off current	V _{EB} =5.0V; I _C =0			200	uA
I _{CEO}	Collector-emitter cut-off current	V _{CE} =40V; I _B =0			0.5	mA
V _{CBO}	Collector-base breakdown voltage					
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =1mA; I _B =0	40			V
V _{EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =3A; I _B =0.3A			1.0	V
V _{CE(sat-2)}	Collector-emitter saturation voltages					
h _{FE-1}	Forward current transfer ratio	I _C =1A; V _{CE} =5V	40			
h _{FE-2}	Forward current transfer ratio					
h _{FE-3}	Forward current transfer ratio					
V _{BE(sat)1}	Base-emitter stauration voltages	I _C =3A; I _B =0.3A			1.5	V
V _{BE(sat)1}	Base-emitter stauration voltages					
f _T	Transition frequency					
C _{ob}	Output Capacitance					